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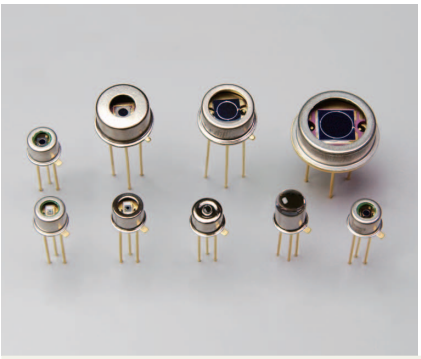
Si APD

S12023 series, etc.



Low bias operation, for 800 nm band

These are 800 nm band near-infrared Si APDs that can operate at low voltages, 200 V or less. They are suitable for applications such as FSO (free space optics) and optical rangefinders.

Features

- **Stable operation at low bias**
- **High-speed response**
- **High sensitivity and low noise**

Applications

- **FSO**
- **Optical rangefinders**

Structure / Absolute maximum ratings

Type no.	Dimensional outline/Window material*1	Package	Effective photosensitive area size*2 (mm)	Absolute maximum ratings		
				Operating temperature Topr (°C)	Storage temperature Tstg (°C)	Soldering conditions
S12023-02	(1)/K	TO-18	φ0.2	-20 to +85	-55 to +125	260 °C or less, within 10 s
S12023-05	(1)/K		φ0.5			
S12051	(2)/L					
S12086	(3)/L					
S12023-10	(1)/K		φ1.0			
S12023-10A*3	(1)/K					
S3884	(4)/K	TO-5	φ1.5			
S2384	(5)/K		φ3.0			
S2385	(6)/K	TO-8	φ5.0			

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.
*1: K=borosilicate glass, L=lens type borosilicate glass
*2: Photosensitive area in which a typical gain can be obtained
*3: This is a variant of the S12023-10 in which the device chip is light-shielded by aluminum layer except for the photosensitive area.

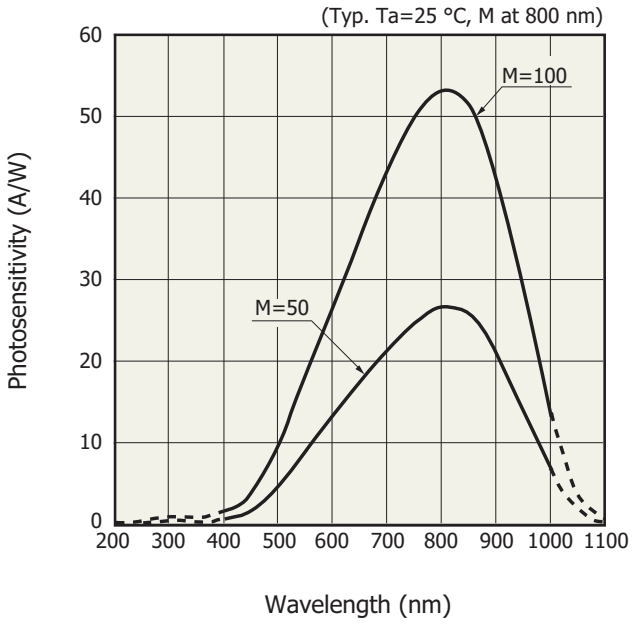
Electrical and optical characteristics (Typ. Ta=25 °C, unless otherwise noted)

Type no.	Spectral response range λ (nm)	Peak*4 sensitivity wavelength λp (nm)	Photo-sensitivity S M=1 λ=800 nm (A/W)	Quantum efficiency QE M=1 λ=800 nm (%)	Breakdown voltage VBR ID=100 μA Typ. (V)	Breakdown voltage VBR ID=100 μA Max. (V)	Temp. co-efficient of VBR (V/°C)	Dark*4 current ID Typ. (nA)	Dark*4 current ID Max. (nA)	Cutoff*4 frequency fc RL=50 Ω (MHz)	Terminal*4 capacitance Ct (pF)	Excess*4 noise figure x λ=800 nm	Gain M λ=800 nm
S12023-02	400 to 1000	800	0.5	75	150	200	0.65	0.05	0.5	1000	1	0.3	100
S12023-05								0.1	1	900	2		
S12051													
S12086													
S12023-10								0.2	2	600	6		
S12023-10A*3													
S3884								0.5	5	400	10		
S2384								1	10	120	40		60
S2385								3	30	40	95		40

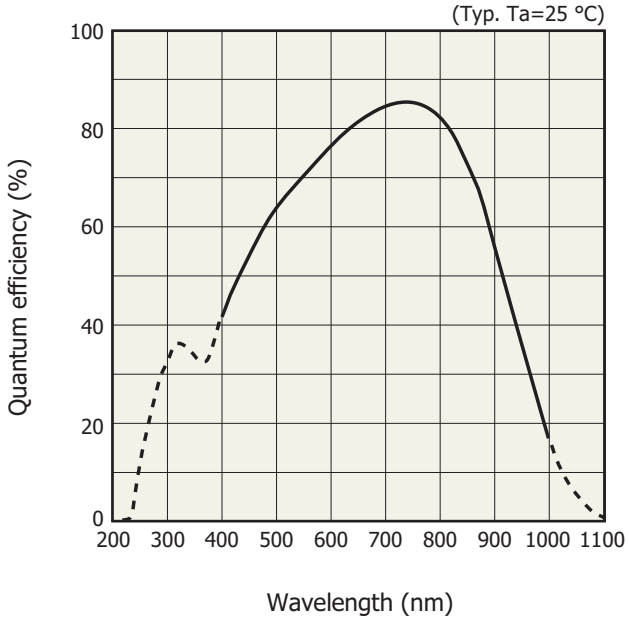
*4: Values measured at a gain listed in the characteristics table

Note: Breakdown voltage can be specified by using the suffix of type number as examples shown below.
S12023-02-01: 80 to 120 V
S12023-02-02: 120 to 160 V
S12023-02-03: 160 to 200 V

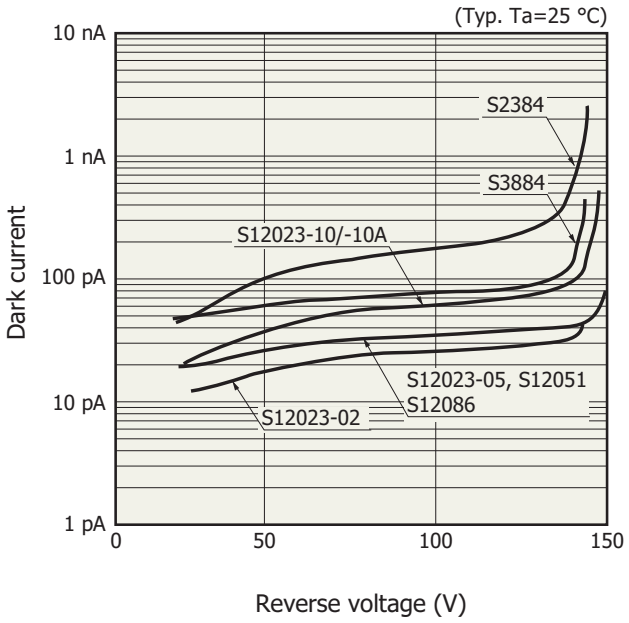
Spectral response



Quantum efficiency vs. wavelength



Dark current vs. reverse voltage



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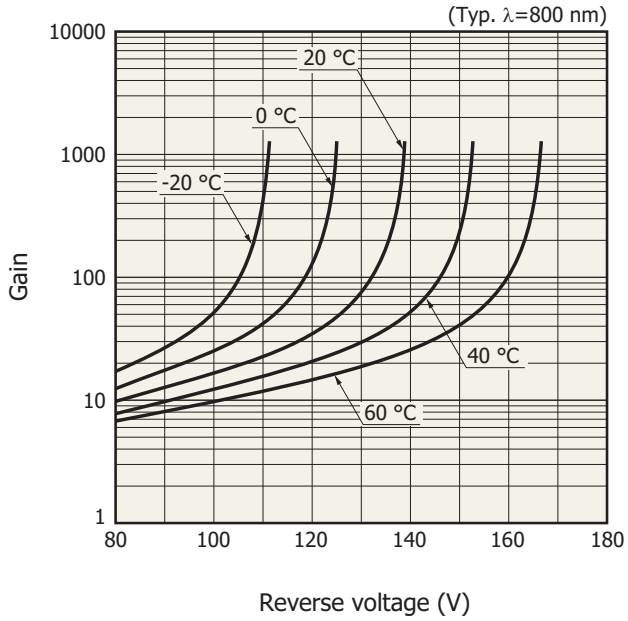
Gain vs. reverse voltage



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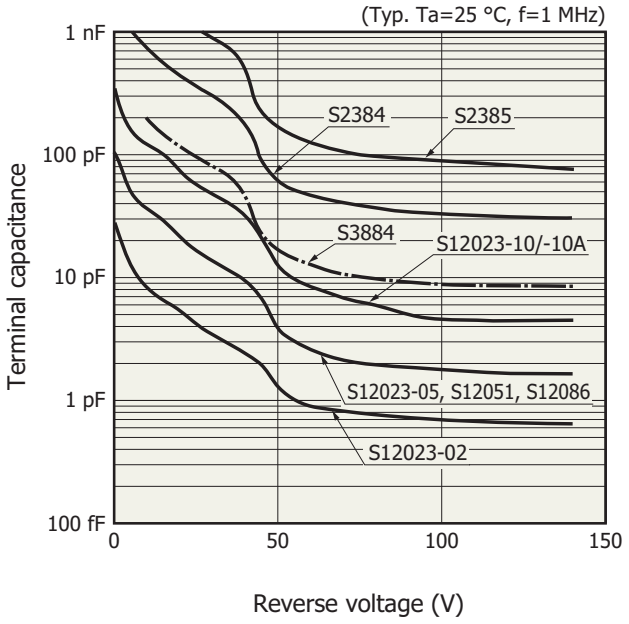
Terminal capacitance vs. reverse voltage



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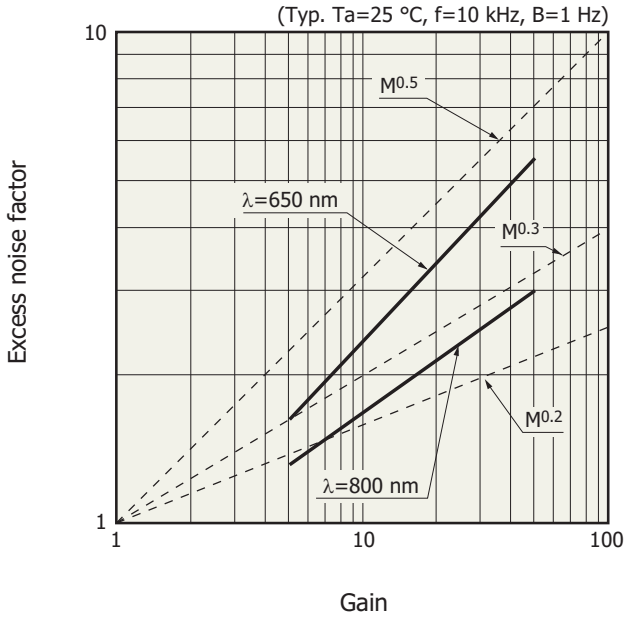
Excess noise factor vs. gain



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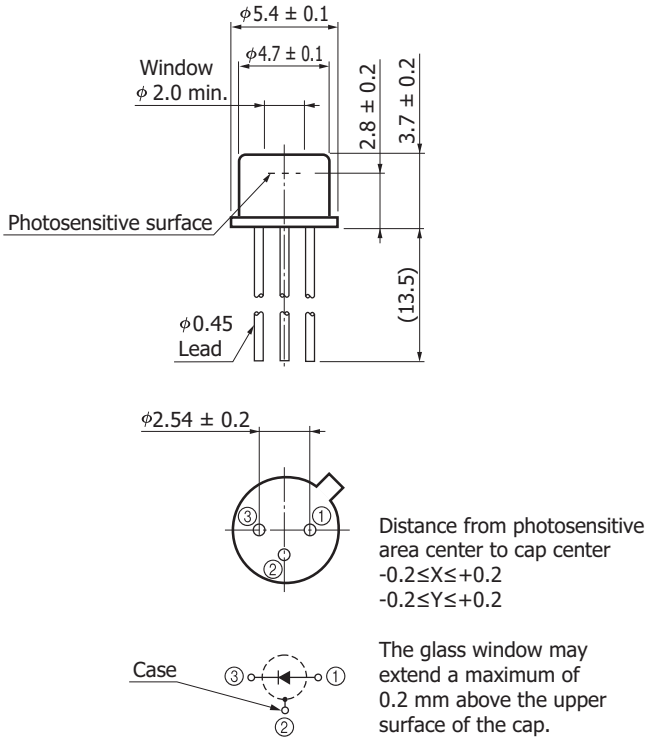
Dimensional outlines (unit: mm)

(1) S12023-02/-05/-10/-10A



Distance from photosensitive area center to cap center
-0.2≤X≤+0.2
-0.2≤Y≤+0.2

The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

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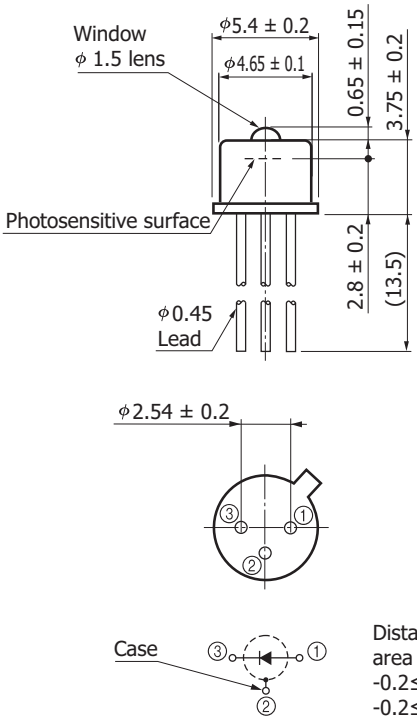
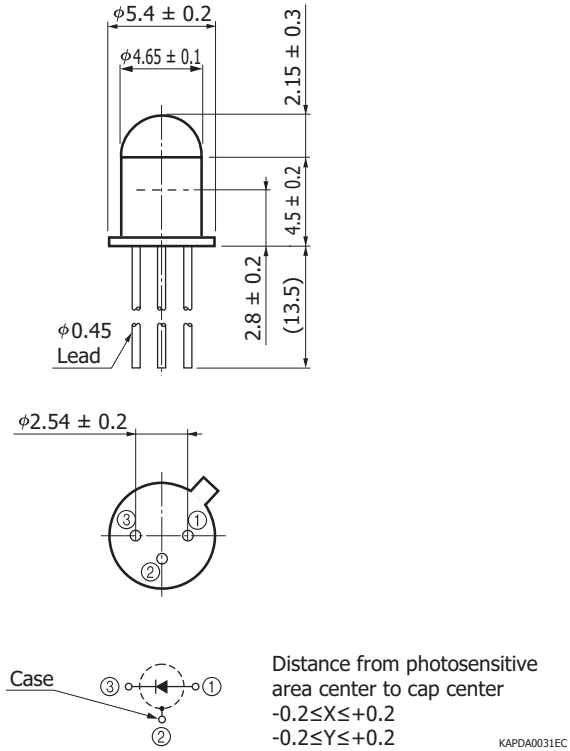
(2) S12051



Distance from photosensitive area center to cap center
-0.2≤X≤+0.2
-0.2≤Y≤+0.2

KAPDA0018EC

(3) S12086



Distance from photosensitive area center to cap center
-0.2≤X≤+0.2
-0.2≤Y≤+0.2

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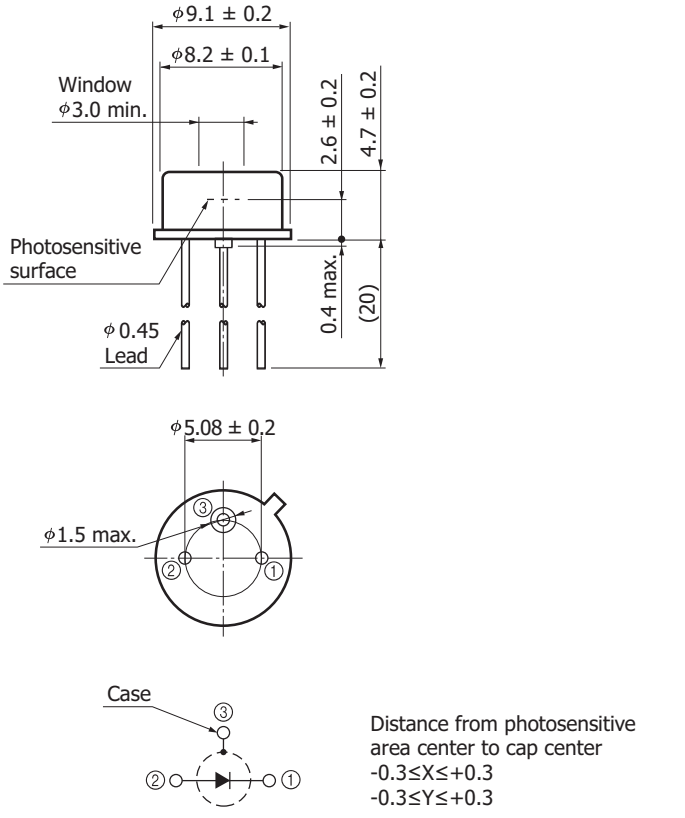
(4) S3884



Distance from photosensitive area center to cap center
-0.3≤X≤+0.3
-0.3≤Y≤+0.3

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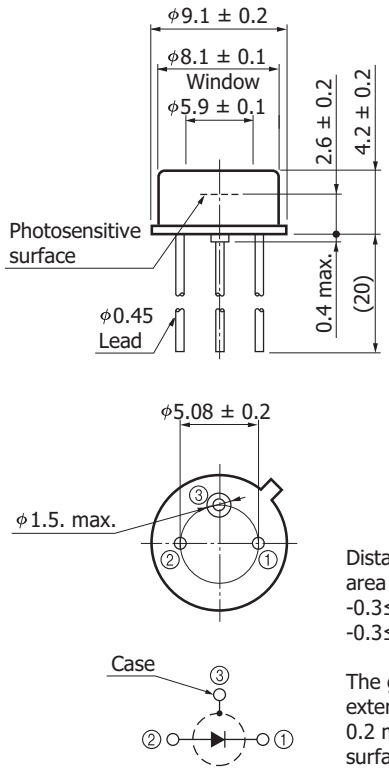
(5) S2384



Distance from photosensitive area center to cap center
-0.3≤X≤+0.3
-0.3≤Y≤+0.3

The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

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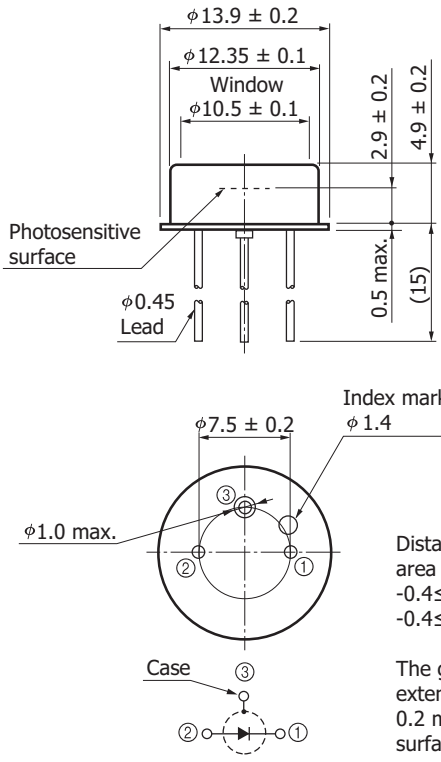
(6) S2385



Distance from photosensitive area center to cap center
-0.4≤X≤+0.4
-0.4≤Y≤+0.4

The glass window may extend a maximum of 0.2 mm above the upper surface of the cap.

KAPDA0013EE

Replacements for previous products

Previous product (listed on the previous datasheet)*	Replacement (listed on this datasheet)
S2381	S12023-02
S2382	S12023-05
S5139	S12051
S8611	S12086
S2383	S12023-10
S2383-10	S12023-10A

* Products that have been removed from this datasheet

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

· Disclaimer
· Metal, ceramic, plastic package products

■ Technical information

· Si APD

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